

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	IRFR7540
▶ Overseas	Part Number	IRFR7540
▶ Equivalent	Part Number	IRFR7540

EV is the abbreviation of name EVVO

V _{DSS} (V)	R _{DS} (ON)	I _D (A)
60	4mΩ(Typ)@V _{GS} =10V	120

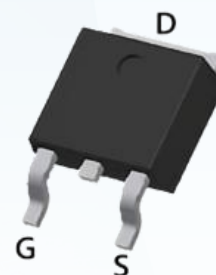
FEATURE:

- The IRFR7540 is the high cell density Split Gate trenchd N-ch MOSFETS, which provides excellent R_{DS(on)} and efficiency for most of the small power switching and load switch applications.

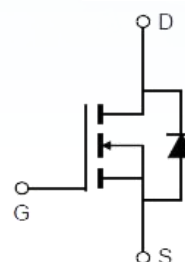
Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Pin Description



TO-252



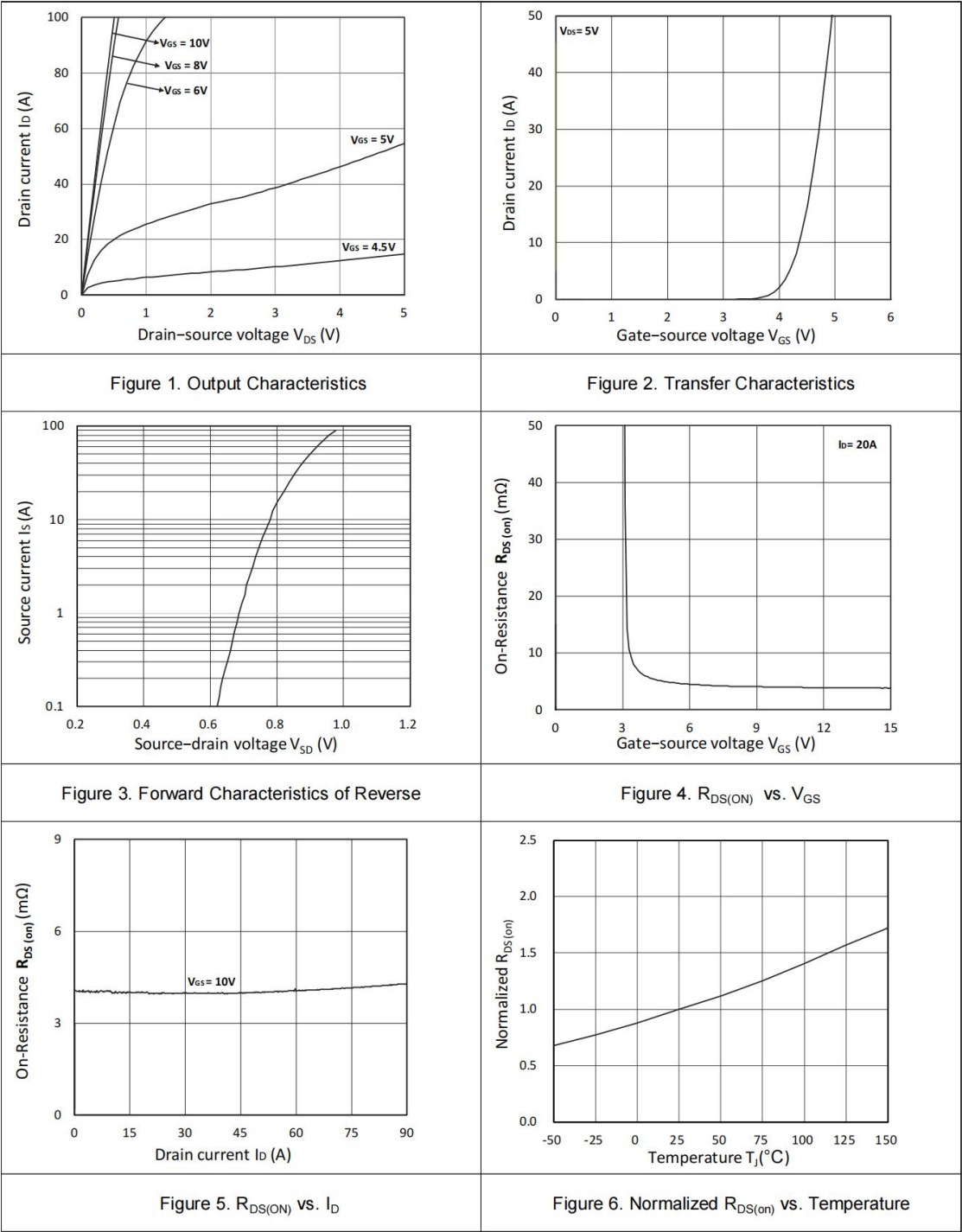
Absolute Maximum Ratings

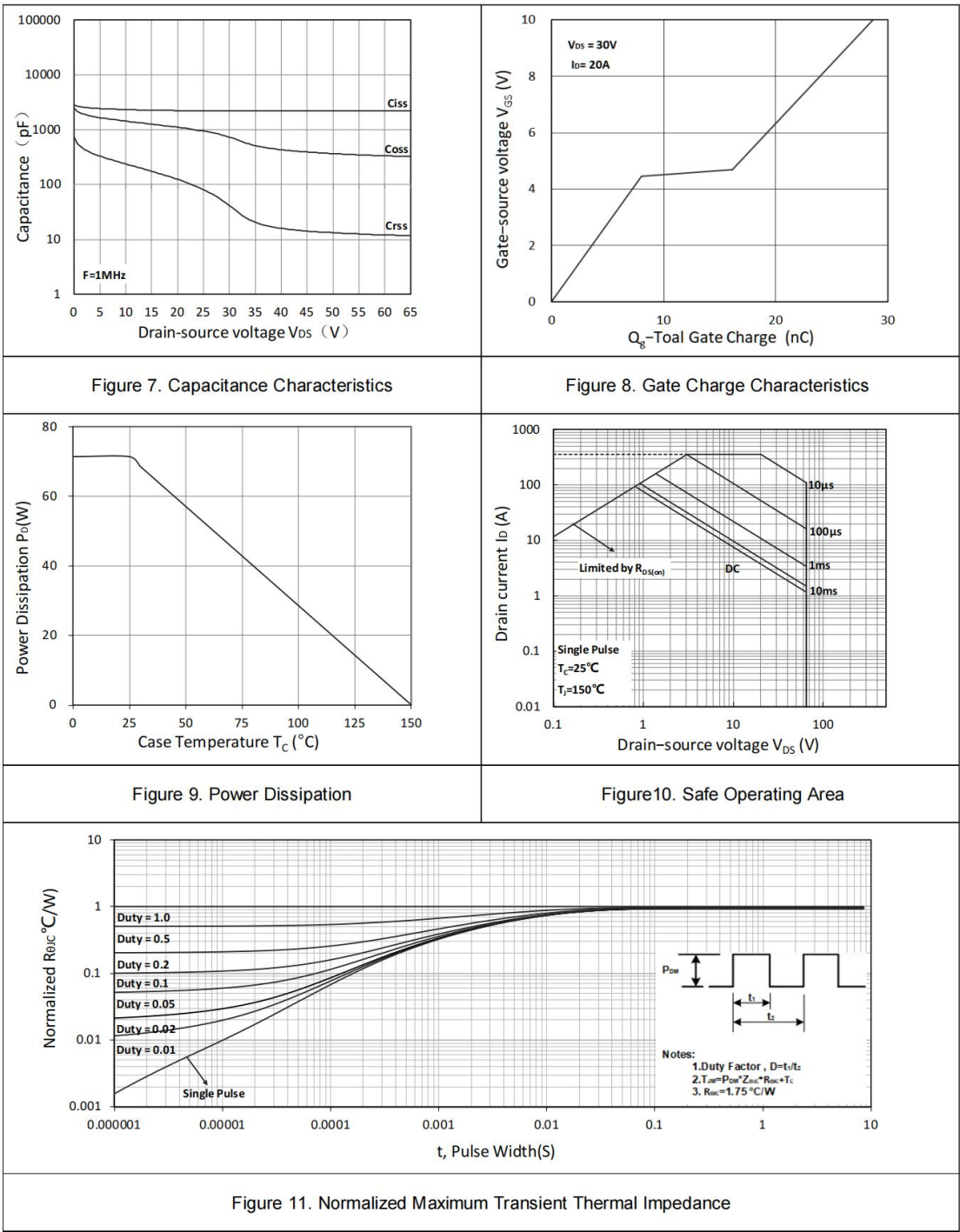
Symbol	Parameter		Rating	Units
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current(V _{GS} = -4.5V)	T _c =25°C	120	A
		T _c =70°C	57	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _{DM}	Pulsed Drain Current		360	A
P _D	Maximum Power Dissipation	T _c =25°C	71.4	W
		T _c =70°C	---	
E _{AS}	Avalanche Energy, Single Pulsed		135.2	mJ
RθJC	Thermal Resistance-Junction to Case		1.75	°C/W
RθJA	Thermal Resistance-Junction to Ambient		58	°C/W

Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

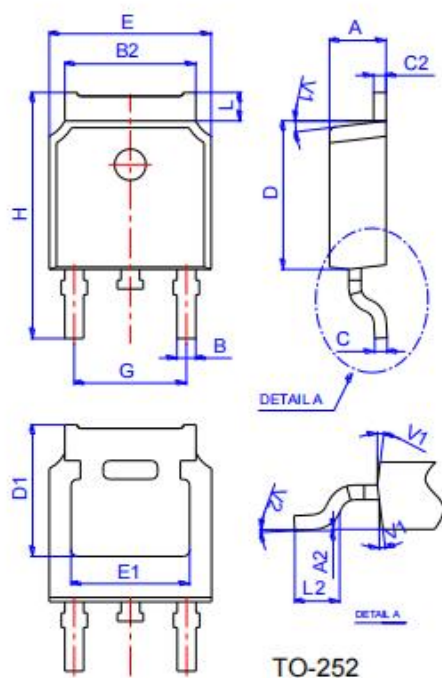
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250uA	60	---	---	V
VGS(th)	Gate threshold voltage	VDS=VGS,ID=250uA	2.5	2.9	3.5	V
RDS(ON)	Drain-Source On-state Resistance	VGS=10V , ID=20A	---	4	5.2	mΩ
IGSS	Gate-source leakage current	VGS=±20V , VDS=0V	---	---	±100	nA
IDSS	Zero gate voltage drain current	VDS=100V,VGS=0V,TJ=25℃	---	---	1	μA
		TJ=100℃	---	---	100	
Dynamic Characteristic						
Ciss	Input Capacitance	VGS=0V, VDS=30V, Frequency=1.0MHz	---	1673	---	pF
Coss	Output Capacitance		---	773	---	
Crss	Reverse Transfer Capacitance		---	46.8	---	
QG	Gate Total Charge	VDS=30V, VGS=10V, IDS=20A	---	28.5	---	nC
Qgs	Gate-Source charge		---	7.8	---	
Qgd	Gate-Drain charge		---	8.4	---	
td(on)	Turn-on delay time	VDD=30V , VGS=10V , RG=3Ω, ID=20A	---	11.2	---	ns
tr	Turn-on Rise Time		---	8.2	---	
td(off)	Turn-off Delay Time		---	19.6	---	
tf	Turn-off Fall Time		---	6.2	---	
RG	Gate Resistance	VGS=0V,VDS=0V,F=1MHz	---	1.8	---	Ω
Diode Characteristics						
Is	Diode Forward Current		--	--	120	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		---	--	----	A
VSD	Diode Forward Voltage	VGS=0V , IS=1A , TJ=25℃	---	---	1.2	V
trr	Reverse Recovery Time	ISD=20A, dISD/dt=-100A/μs	---	50	---	ns
Qrr	Reverse Recovery Charge		---	20	---	nC

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



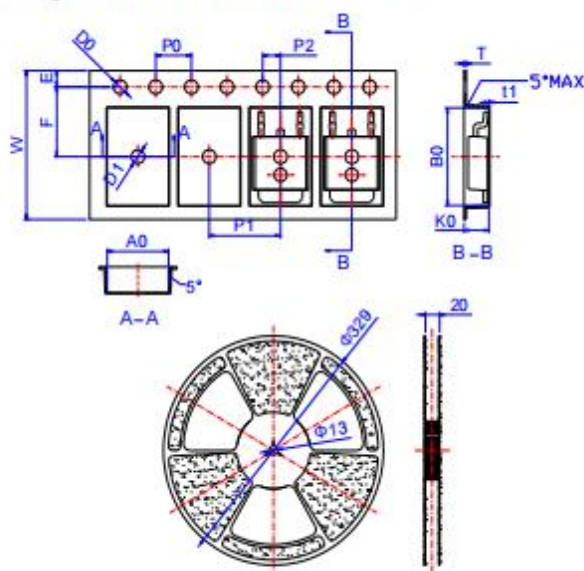


Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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